

G2N5401

PNP EPITAXIAL PLANAR TRANSISTOR

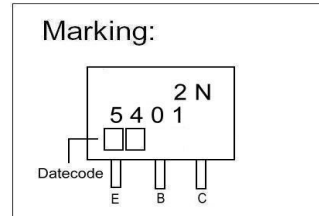
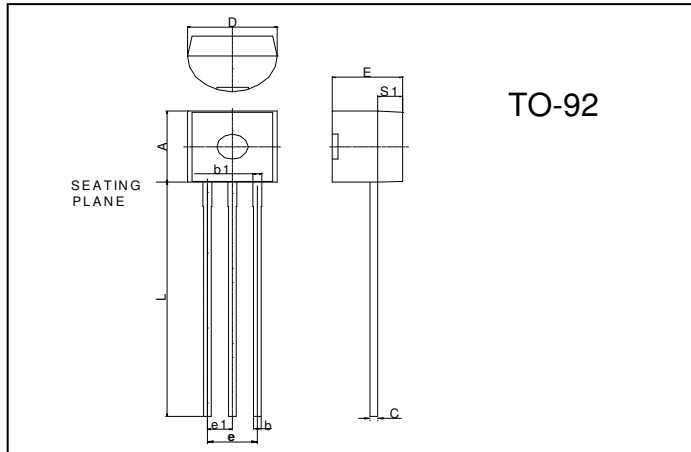
Description

The G2N5401 is designed for general purpose applications requiring high breakdown voltages.

Features

- *Complementary to NPN Type G2N5551
- *High Collector-Emitter Breakdown Voltage ($V_{CE0}=150V@I_C=1mA$)

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ C$
Collector to Base Voltage	V_{CBO}	-160	V
Collector to Emitter Voltage	V_{CEO}	-150	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Total Power Dissipation	P_D	625	mW

Characteristics at $T_a = 25^\circ C$

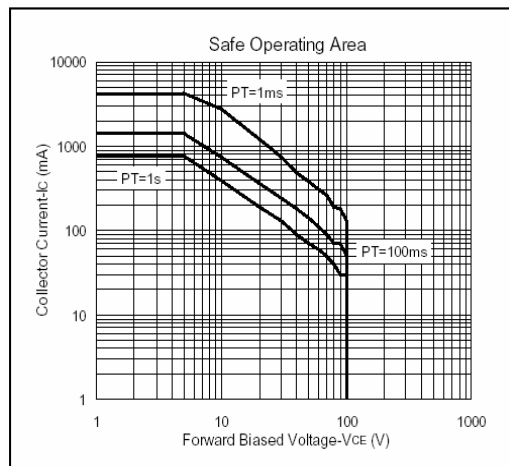
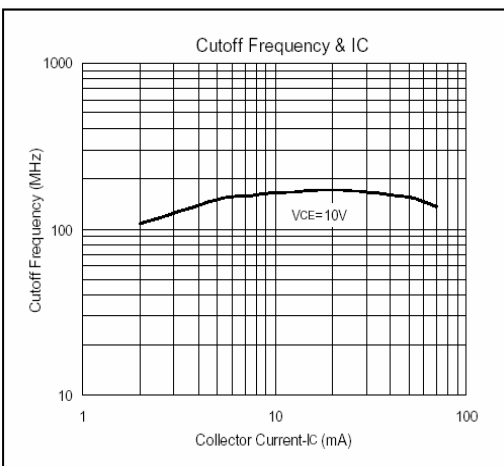
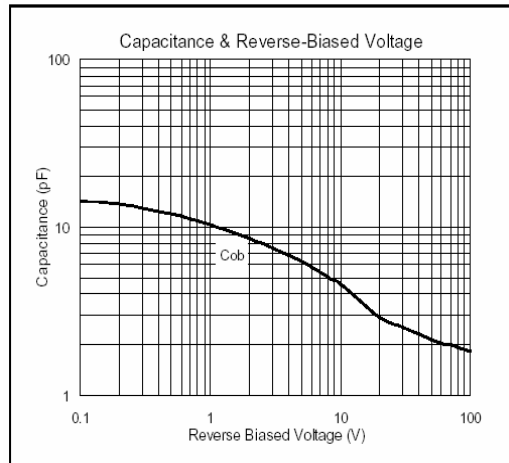
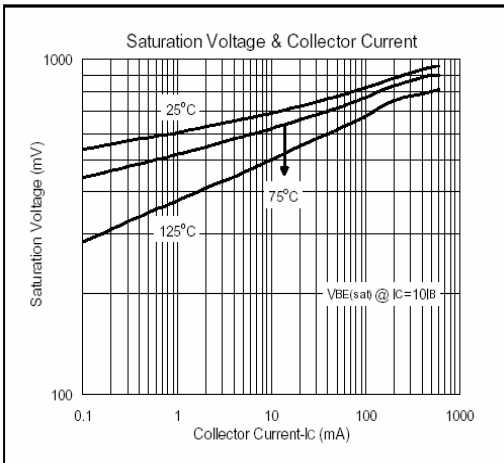
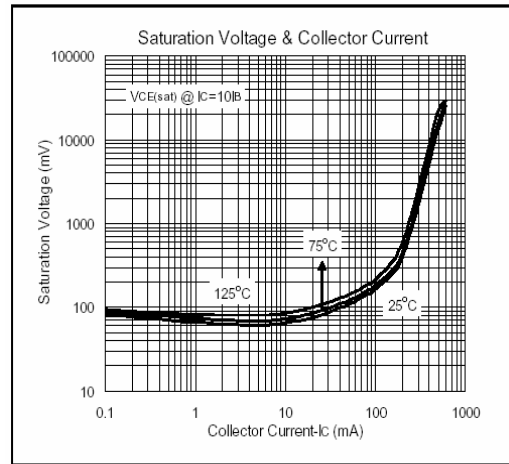
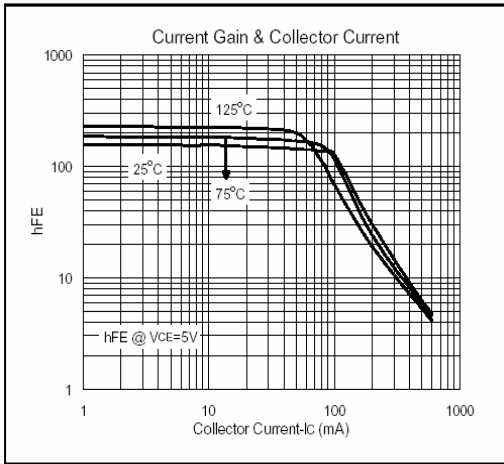
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CBO}	-160	-	-	V	$I_C = -100\mu A, I_E = 0$
V_{CEO}	-150	-	-	V	$I_C = -1mA, I_B = 0$
V_{EBO}	-5	-	-	V	$I_E = -10\mu A, I_C = 0$
I_{CBO}	-	-	-50	nA	$V_{CB} = -120V, I_E = 0$
I_{EBO}	-	-	-50	nA	$V_{EB} = -3V, I_C = 0$
* $V_{CE(sat)1}$	-	-	-0.2	V	$I_C = -10mA, I_B = -1mA$
* $V_{CE(sat)2}$	-	-	-0.5	mV	$I_C = -50mA, I_B = -5mA$
* $V_{BE(sat)1}$	-	-	-1	V	$I_C = -10mA, I_B = -1mA$
* $V_{BE(sat)2}$	-	-	-1	V	$I_C = -50mA, I_B = -5mA$
* h_{FE1}	50	-	-		$V_{CE} = -5V, I_B = -1mA$
* h_{FE2}	80	160	400		$V_{CE} = -5V, I_C = -10mA$
* h_{FE3}	50	-	-		$V_{CE} = -5V, I_C = -50mA$
f_T	100	-	300	MHz	$V_{CE} = -10V, I_C = -10mA, f = 100MHz$
C_{ob}	-	-	6	pF	$V_{CB} = -10V, f = 1MHz, I_E = 0$

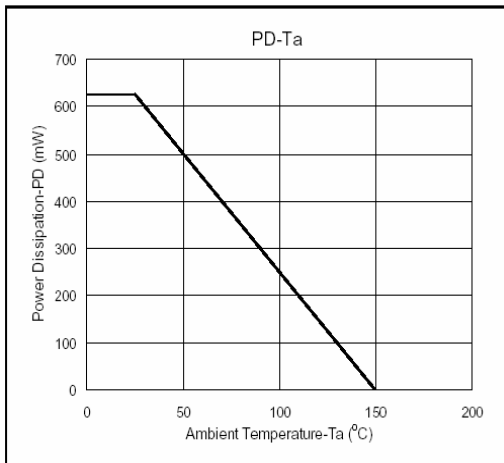
* Pulse Test: Pulse Width $\leq 380\mu s$, Duty Cycle $\leq 2\%$

Classification Of h_{FE2}

Rank	A	N	C
Range	80-200	100-240	160-400

Characteristics Curve





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